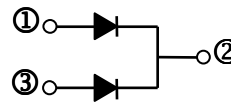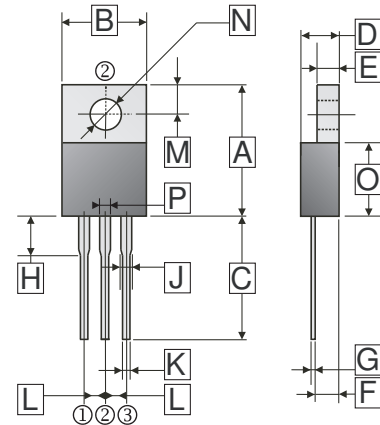SeCoS
Elektronische Bauelemente

RoHS Compliant Product
A suffix of "-C" specifies halogen free

FEATURES

- Planar MOS Schottky technology
- Low forward voltage drop
- High current capability
- High reliability
- High surge current capability
- Epitaxial construction

TO-220

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	14.22	16.51	J	0.7	1.78
B	9.57	10.90	K	0.38	1.11
C	12.50	14.75	L	2.01	3.07
D	3.56	5.10	M	2.22	3.43
E	0.51	1.47	N	3.10	4.31
F	2.03	3.19	O	8.10	9.65
G	0.28	0.76	P	1.18 Typ.	
H	2.95	4.5			

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Rating 25℃ ambient temperature unless otherwise s pecified. Single phase half wave, 60Hz, resistive or inductive load.
For capacitive load, de-rate current by 20%.)

Parameter		Symbol	Rating	Unit
Maximum Recurrent Peak Reverse Voltage		V_{RRM}	60	V
Working Peak Reverse Voltage		V_{RSM}	60	V
Maximum DC Blocking Voltage		V_{DC}	60	V
Maximum Average Forward Rectified Current	(Per Leg)	I_F	20	A
	(Per Device)		40	
Peak Forward Surge Current@ 8.3 ms single half sine-wave superimposed on rated load (JEDEC method)		I_{FSM}	280	A
Voltage Rate of Chance (Rated V_R)		dv/dt	10000	V / μs
Typical Thermal Resistance from Junction to Case		$R_{\theta JC}$	2	℃ /W
Operating and Storage Temperature Range		T_J, T_{STG}	-40~150	℃

ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Typ.	Max.	Unit	Test Condition
Maximum Instantaneous Forward Voltage	V_F	0.35	0.39	V	I_F=3A, T_J=25℃
		0.38	0.42		I_F=5A, T_J=25℃
		0.56	0.6		I_F=20A, T_J=25℃
		0.53	-		I_F=20A, T_J=125℃
Maximum DC Reverse Current at Rated DC Blocking Voltage [2]	I_R	-	0.5	mA	T_J=25℃
		-	30		T_J=100℃
Typical Junction Capacitance [1]	C_J	600	-	pF	

Notes:
1. Measured at 1MHz and applied reverse voltage of 5.0V D.C.
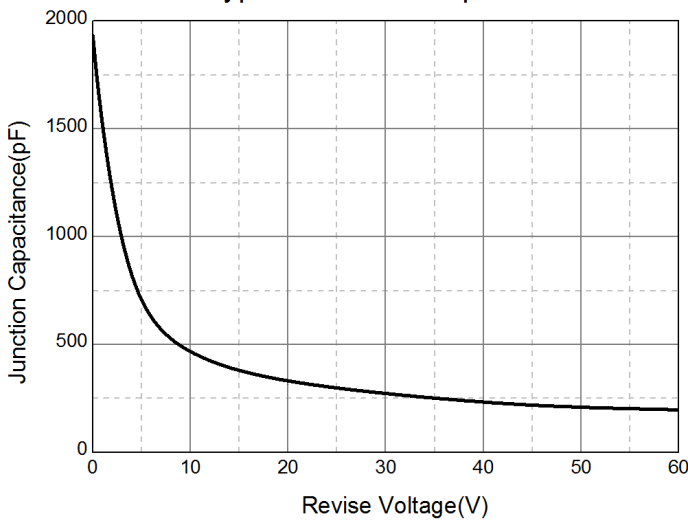2. Pulse Test：Pulse width=300μs, duty cycle≦2.0%.

SECOS
Elektronische Bauelemente
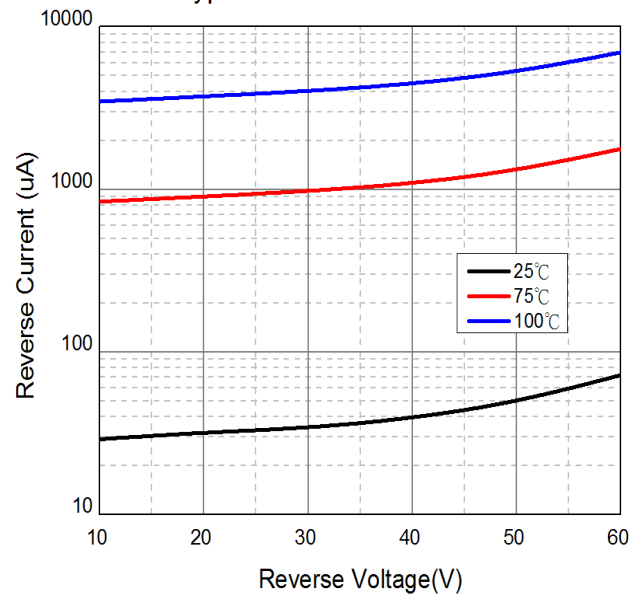
CHARACTERISTIC CURVES

Typical Forward Current Derating Curve
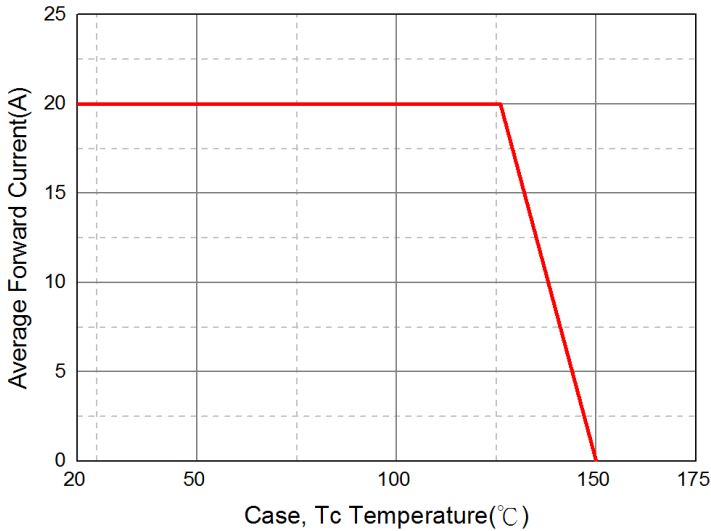
Typical Forward Characteristic

Typical Junction Capacitance
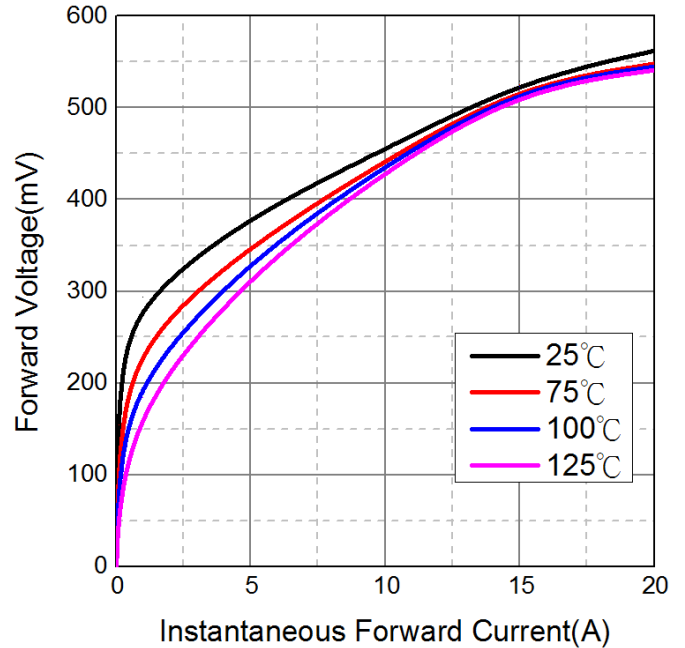
Maximum Non-Repetitive Forward Surge Current

Typical Reverse Characteristic